

CMXT2222A

SURFACE MOUNT  
DUAL NPN  
SILICON TRANSISTORS



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXT2222A type is a dual NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose and switching applications.

**MARKING CODE: X1P**



**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

**SYMBOL**

$V_{CBO}$  75  
 $V_{CEO}$  40  
 $V_{EBO}$  6.0  
 $I_C$  600  
 $P_D$  350  
 $T_J, T_{stg}$  -65 to +150  
 $\theta_{JA}$  357

**UNITS**

V  
V  
V  
mA  
mW  
 $^\circ\text{C}$   
 $^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=60V$		10	nA
$I_{CBO}$	$V_{CB}=60V, T_A=125^\circ\text{C}$		10	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=60V, V_{EB}=3.0V$		10	nA
$I_{EBO}$	$V_{EB}=3.0V$		10	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	75		V
$BV_{CEO}$	$I_C=10\text{mA}$	40		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=10V, I_C=0.1\text{mA}$	35		
$h_{FE}$	$V_{CE}=10V, I_C=1.0\text{mA}$	50		
$h_{FE}$	$V_{CE}=10V, I_C=10\text{mA}$	75		
$h_{FE}$	$V_{CE}=10V, I_C=150\text{mA}$	100	300	
$h_{FE}$	$V_{CE}=1.0V, I_C=150\text{mA}$	50		
$h_{FE}$	$V_{CE}=10V, I_C=500\text{mA}$	40		
$f_T$	$V_{CE}=20V, I_C=20\text{mA}, f=100\text{MHz}$	300		MHz
$C_{ob}$	$V_{CB}=10V, I_E=0, f=1.0\text{MHz}$		8.0	pF
$C_{ib}$	$V_{EB}=0.5V, I_C=0, f=1.0\text{MHz}$		25	pF
$h_{ie}$	$V_{CE}=10V, I_C=1.0\text{mA}, f=1.0\text{kHz}$	2.0	8.0	k $\Omega$
$h_{ie}$	$V_{CE}=10V, I_C=10\text{mA}, f=1.0\text{kHz}$	0.25	1.25	k $\Omega$

R3 (12-February 2010)

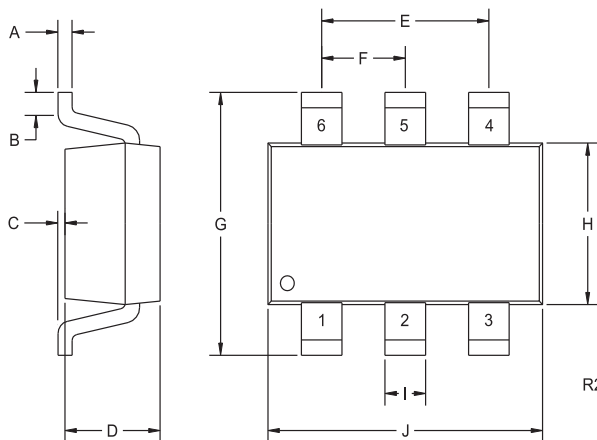
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**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$h_{re}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$		8.0	$\times 10^{-4}$
$h_{re}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$		4.0	$\times 10^{-4}$
$h_{fe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	300	
$h_{fe}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	75	375	
$h_{oe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	5.0	35	$\mu\text{S}$
$h_{oe}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	25	200	$\mu\text{S}$
$rb'C_c$	$V_{CB}=10\text{V}, I_E=20\text{mA}, f=31.8\text{MHz}$		150	ps
NF	$V_{CE}=10\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega, f=1.0\text{kHz}$		4.0	dB
$t_d$	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$		10	ns
$t_r$	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$		25	ns
$t_s$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		225	ns
$t_f$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		60	ns

**SOT-26 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

**MARKING CODE: X1P**

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